Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0606-3 (SOT8001) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small and ultra thin SMD plastic package: 0.62 x 0.62 x 0.37 mm
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	770	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 770 \text{ mA}; T_j = 25 \text{ °C}$		-	550	670	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0606-3 (SOT8001)	G S 017aaa255

6. Ordering information

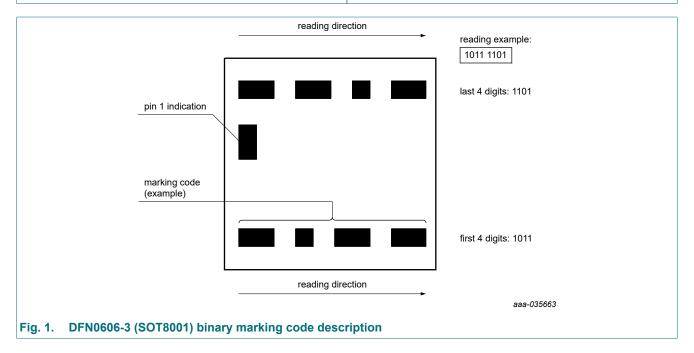
Table 3. Ordering information

Type number			
	Name	Description	Version
PMH550UNEA		plastic, leadless ultra small package; 3 terminals; body 0.62 x 0.62 x 0.37 mm	SOT8001

7. Marking

Table 4. Marking codes

Type number	Marking code
PMH550UNEA	0011
	0111



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	770	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	485	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	3	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	380	mW
			[1]	-	710	mW
		T _{sp} = 25 °C		-	2.8	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-draii	n diode		'			
Is	source current	T _{amb} = 25 °C	[1]	-	680	mA
ESD maximu	um rating			'		,
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm 2 .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

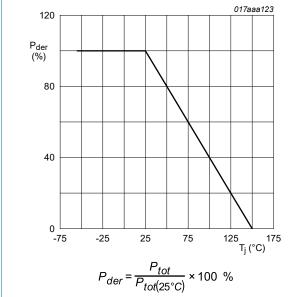


Fig. 2. Normalized total power dissipation as a function of junction temperature

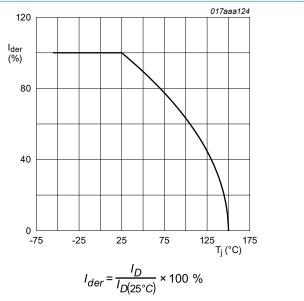


Fig. 3. Normalized continuous drain current as a function of junction temperature

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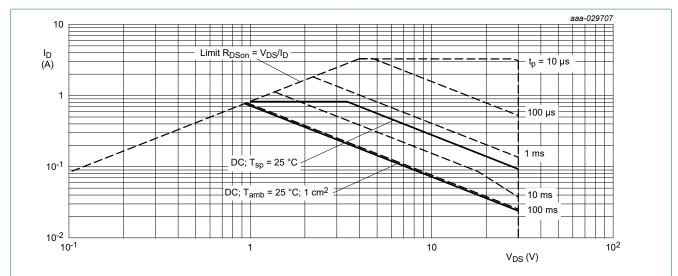


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	285	330	K/W
junction to ambient	junction to ambient		[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	38	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

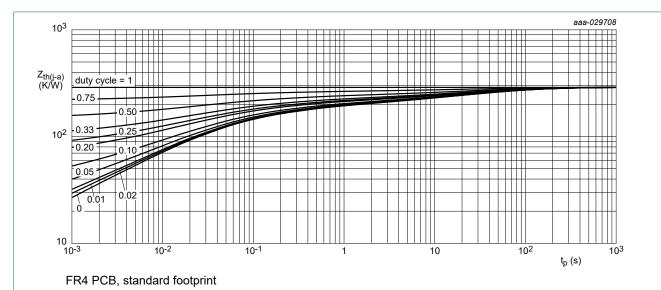


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

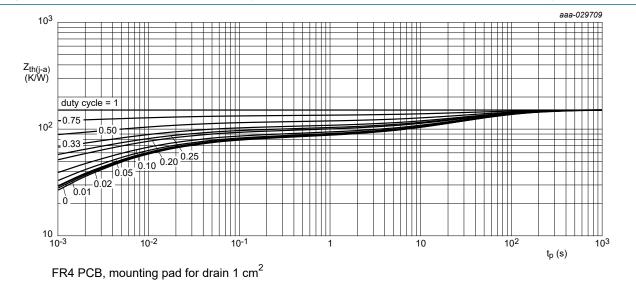


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	0.95	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 770 mA; T _j = 25 °C	-	550	670	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 770 mA; T _j = 150 °C	-	990	1200	mΩ
		V _{GS} = 2.5 V; I _D = 770 mA; T _j = 25 °C	-	660	900	mΩ
		V _{GS} = 1.8 V; I _D = 80 mA; T _j = 25 °C	-	770	1120	mΩ
		$V_{GS} = 1.5 \text{ V}; I_D = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	890	1500	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 770 \text{ mA}; T_j = 25 \text{ °C}$	-	2.2	-	S
R _G	gate resistance	f = 1 MHz	-	19	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 770 mA; V _{GS} = 4 V;	-	0.38	0.4	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	30.3	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.1	-	pF
C _{rss}	reverse transfer capacitance		-	3.7	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 770 mA; V _{GS} = 4 V;	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time	1	-	4	-	ns
t _f	fall time	1	-	2	-	ns
Source-drai	in diode		<u> </u>	-	1	'
V_{SD}	source-drain voltage	I _S = 680 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.9	1.2	V

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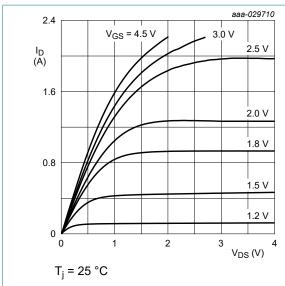


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

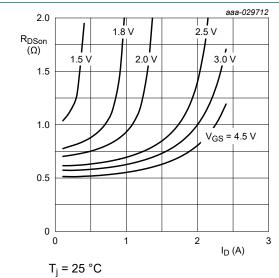


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

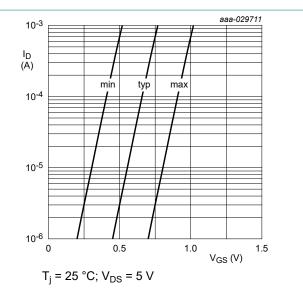


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

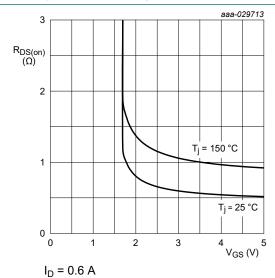


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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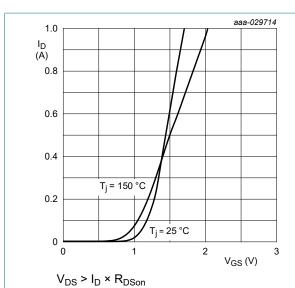


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

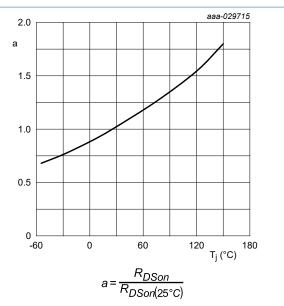


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

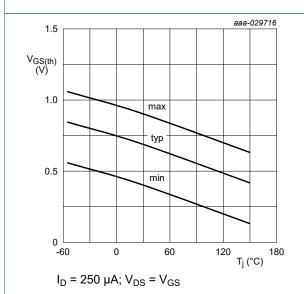
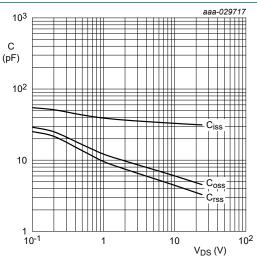


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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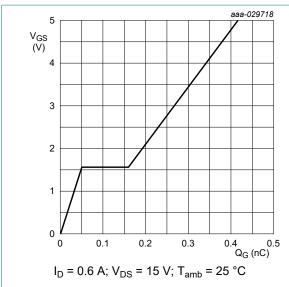


Fig. 15. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

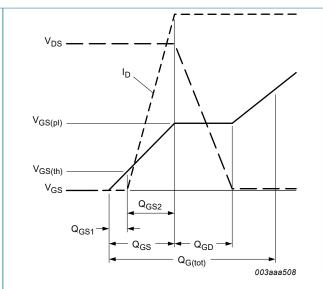


Fig. 16. Gate charge waveform definitions

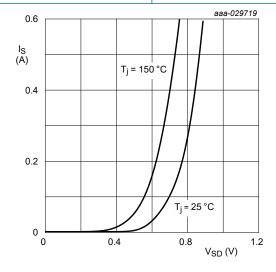
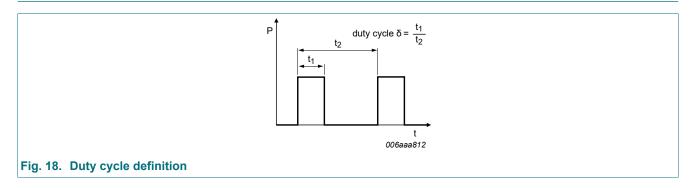


Fig. 17. Source current as a function of source-drain voltage; typical values

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11. Test information

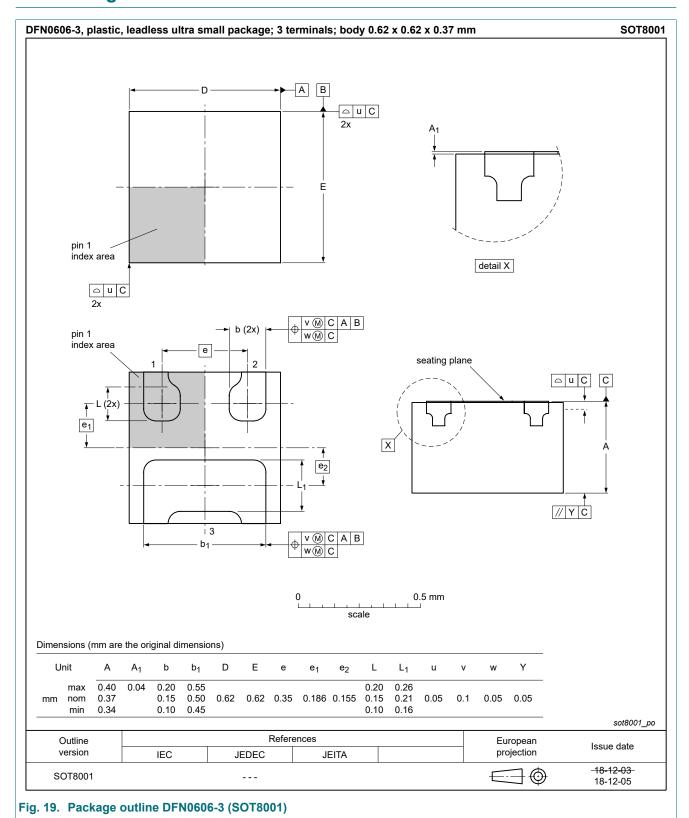


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

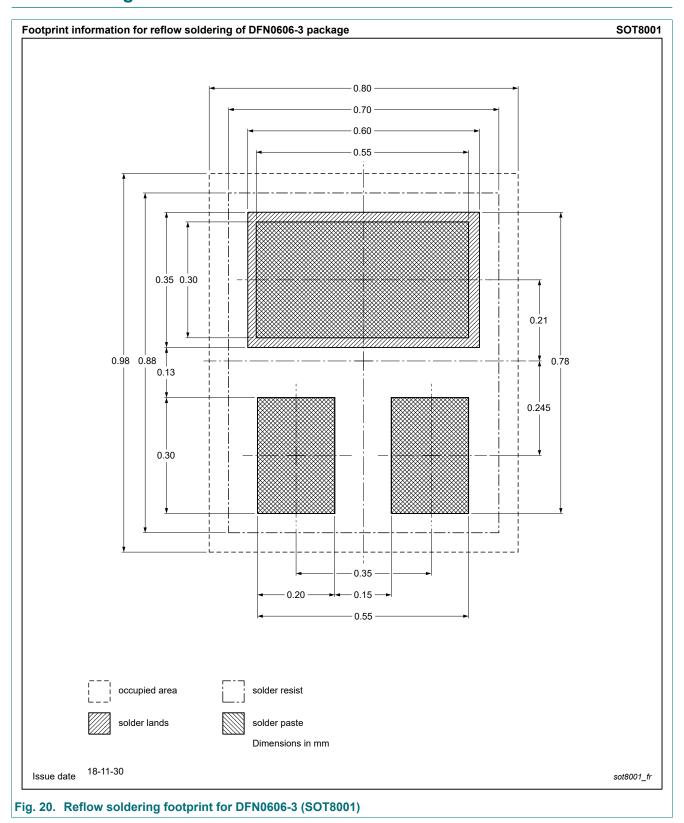
30 V, N-channel Trench MOSFET

12. Package outline



30 V, N-channel Trench MOSFET

13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMH550UNEA v.1	20240711	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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